

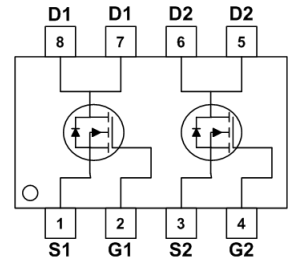
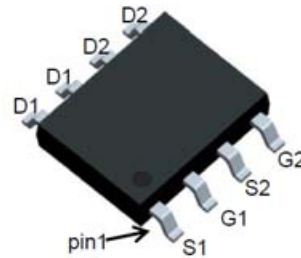
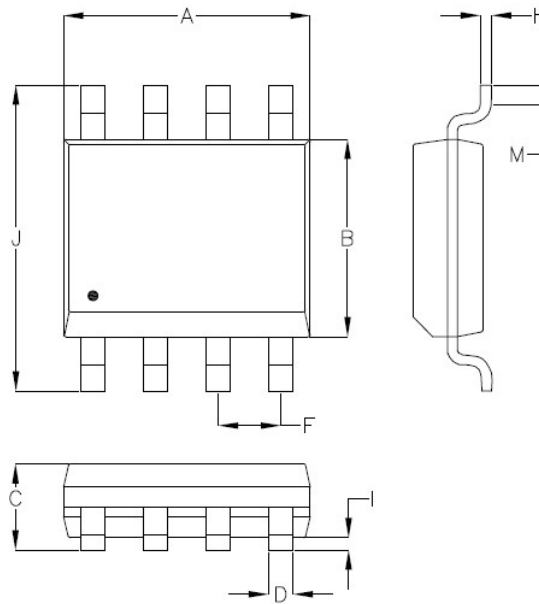
Dual N-Channel Enhancement Mode Power MOSFET
● Features

$V_{DS} = 30V$
 $I_D = 10A$
 $R_{DS(ON)} \leq 12m\Omega (V_{GS} = 10V)$

● General Description

The TDNM1230UX is the high cell density trench N-ch MOSFETs, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The TDNM1230UX meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

● Pin Configurations

● Package Information
SOP8


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.700	5.150	0.185	0.203
B	3.700	4.100	0.146	0.161
C	1.23	1.753	0.048	0.069
D	0.310	0.510	0.012	0.020
F	1.070	1.470	0.042	0.058
H	0.160	0.254	0.006	0.010
I	0.050	0.254	0.002	0.010
J	5.750	6.250	0.226	0.246
M	0.400	1.270	0.016	0.050

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● Absolute Maximum Ratings (@TA=25°C unless otherwise noted)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate Source Voltage		V_{GSS}	±20	V
Drain Current (Continuous) *AC	TA=25°C	I_D	10	A
	TA=100°C		8	
Drain Current (Pulse) *B		I_{DM}	36	A
Power Dissipation	TA=25°C	P_D	1.5	W
	TA=100°C		1.0	
Operating Temperature/ Storage Temperature		T_J/T_{STG}	-55~150	°C
Single Pulse Avalanche Energy		E_{AS}	24.2	mJ
Thermal Resistance ,Junction-to-Ambient		$R_{\theta JA}$	85	°C/W

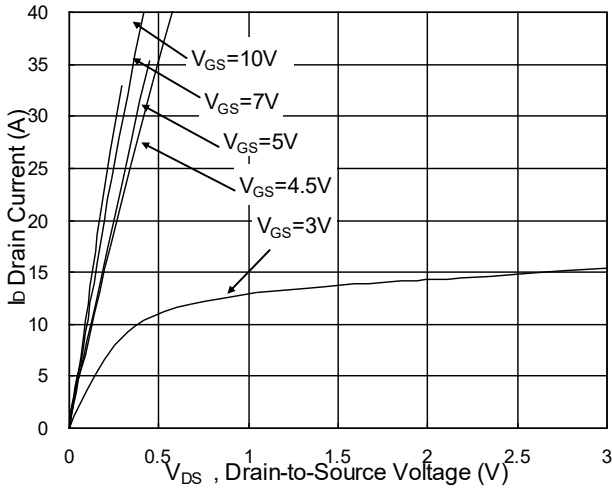
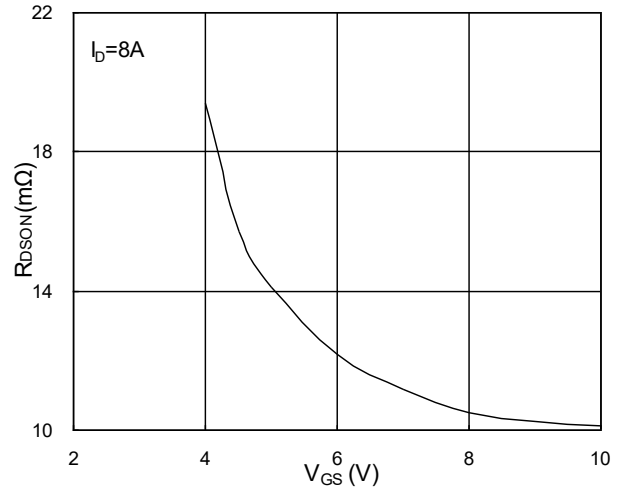
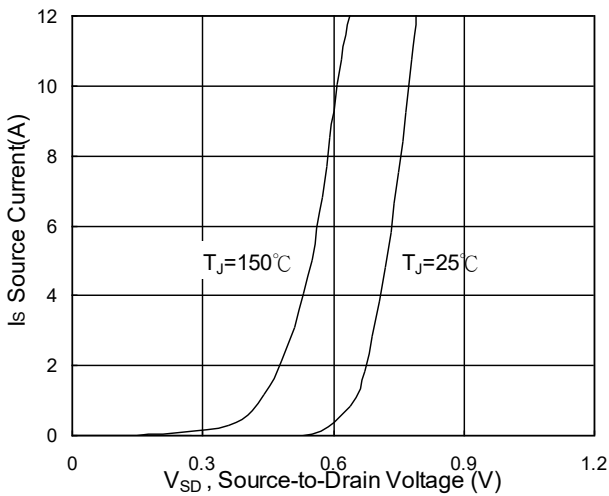
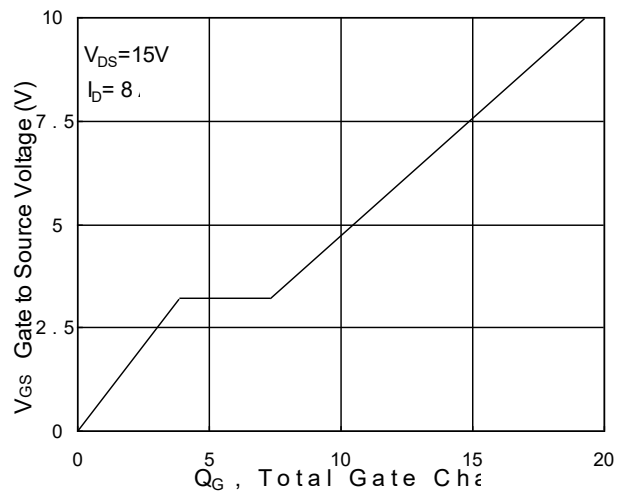
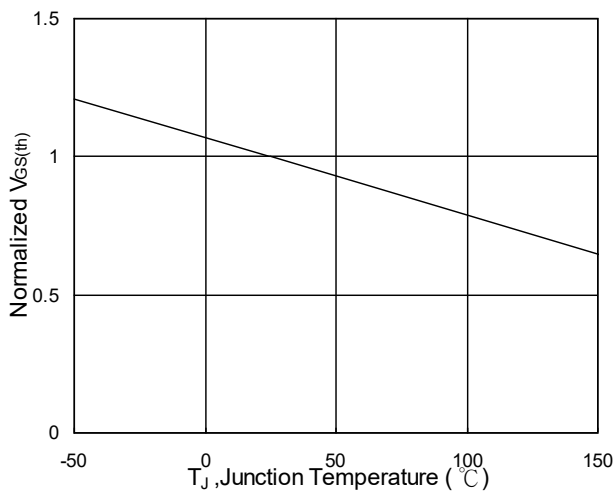
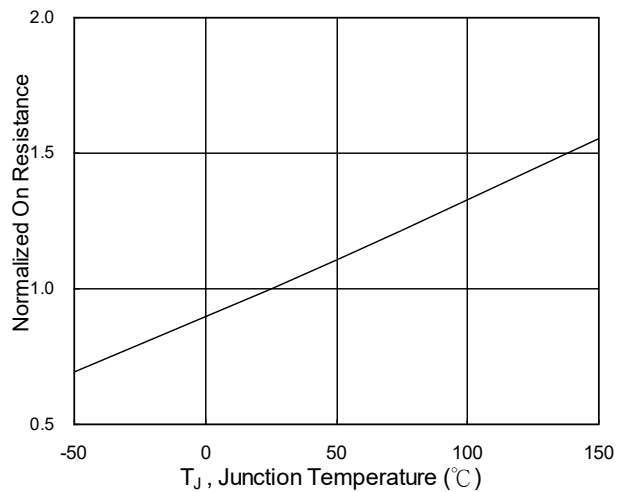
● Electrical Characteristics (@TA=25°C unless otherwise noted)

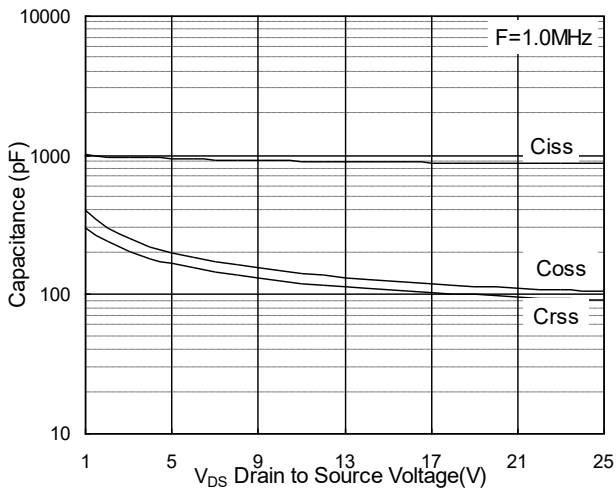
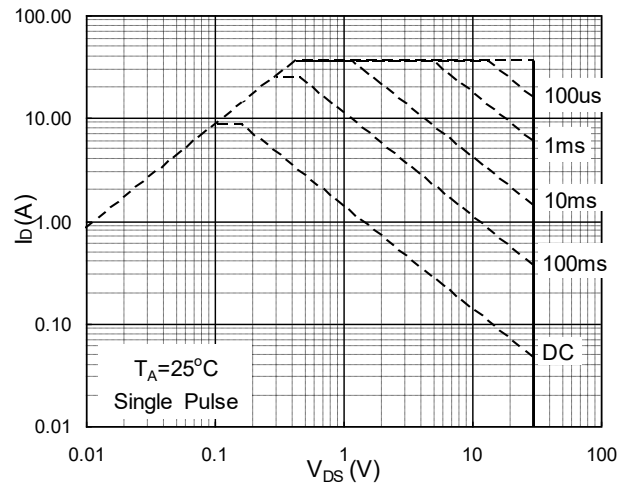
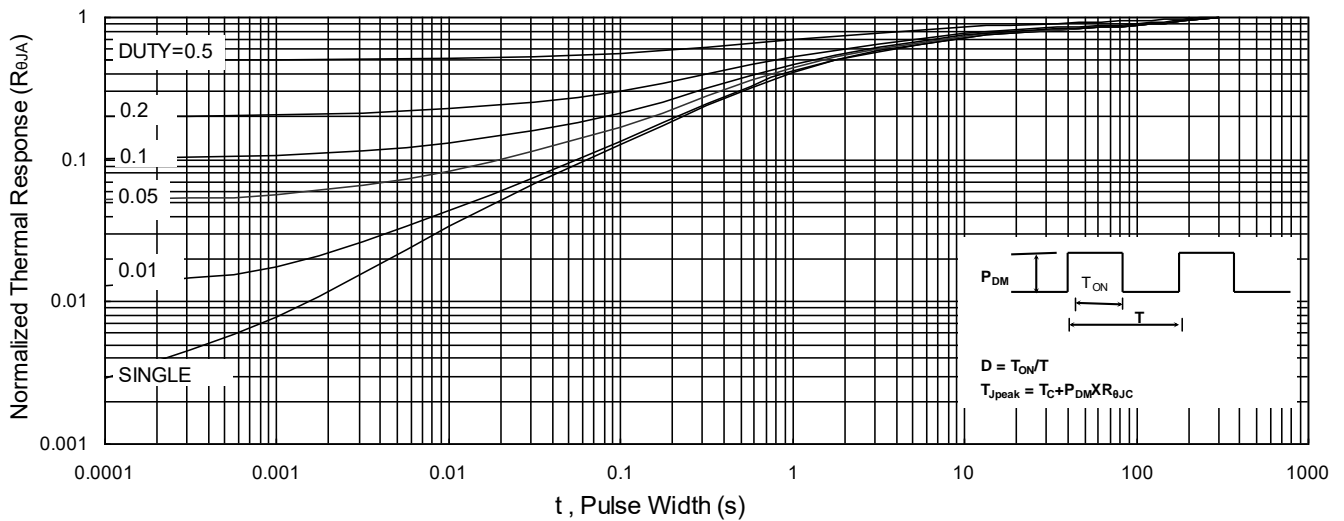
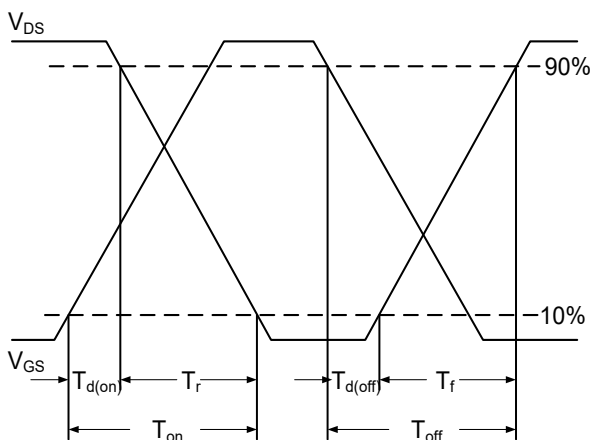
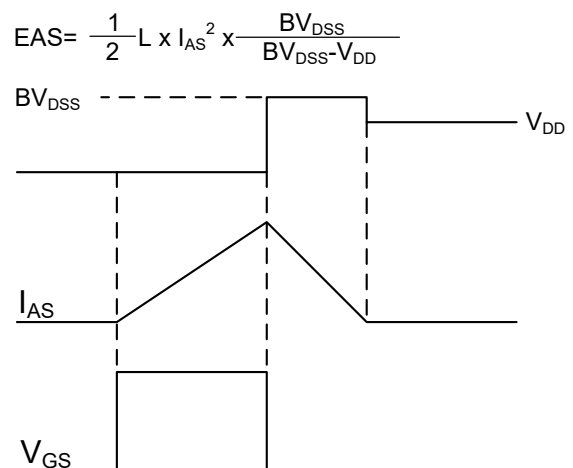
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	--	--	1	uA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1.2	--	2.5	V
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	±100	nA
Drain-Source On-state Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$	--	--	12	mΩ
		$V_{GS}=4.5V, I_D=6A$	--	--	18	mΩ
Diode Forward Voltage	V_{SD}	$I_{SD}=1A, V_{GS}=0V$	--	--	1	V
Switching						
Total Gate Charge	Q_g	$V_{GS}=4.5V, V_{DS}=15V, I_D=8A$	--	9.6	--	nC
Gate- Source Charge	Q_{gs}		--	3.9	--	nC
Gate- Drain Charge	Q_{gd}		--	3.4	--	nC
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DD}=15V, I_D=8A, R_{GEN}=1.5\Omega$	--	4.2	--	ns
Turn-on Rise Time	t_r		--	8.2	--	ns
Turn-off Delay Time	$t_{d(off)}$		--	31	--	ns
Turn-off Fall Time	t_f		--	4	--	ns
Dynamic						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=15V, f=1MHz$	--	940	--	pF
Output Capacitance	C_{oss}		--	131	--	pF
Reverse Transfer Capacitance	C_{rss}		--	109	--	pF

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA=25C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature .

C: The current rating is based on the $t < 10s$ junction to ambient thermal resistance rating.

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● TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs. G-S Voltage

Fig.3 Source Drain Forward Characteristics

Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

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